1 Characteristics

Table 2: Absolute maximum ratings (limiting values), T_j = 25 °C unless otherwise specified

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (180 ° conduction angle)		T_c = 132 °C	20	A
$I_{T(AV)}$	Average on-state current (180 ° conduction angle)		T_c = 132 °C	12.7	A
			T_c = 137 °C	10	
			T_c = 140 °C	8	
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25 °C)		t_p = 8.3 ms	197	A
			t_p = 10 ms	180	
I^2t	I^2t value for fusing		t_p = 10 ms	162	A^2s
dI/dt	Critical rate of rise of on-state current I_G = 2 x I_{GT}, tr ≤ 100 ns		f = 60 Hz	100	A/µs
V_{DSM}/V_{RSM}	Non repetitive surge peak off-state voltage		t_p = 10 ms	700	V
I_{GM}	Peak gate current	t_p = 20 µs	T_j = 150 °C	4	A
$P_{G(AV)}$	Average gate power dissipation		T_j = 150 °C	1	W
V_{RGM}	Maximum peak reverse gate voltage			5	V
T_{stg}	Storage junction temperature range			-40 to +150	°C
T_j	Operating junction temperature range			-40 to +150	°C

Table 3: Electrical characteristics (T_j = 25 °C unless otherwise specified)

Symbol	Test conditions			Value	Unit
I_{GT}	V_D = 12 V, R_L = 33 Ω		Typ.	5	mA
			Max.	10	
V_{GT}			Max.	1.3	V
V_{GD}	V_D = V_{DRM}, R_L = 3.3 kΩ	T_j = 150 °C	Min.	0.1	V
I_H	I_T = 500 mA, gate open		Max.	40	mA
I_L	I_G = 1.2 x I_{GT}		Max.	60	mA
dV/dt	V_D = 402 V, gate open	T_j = 150 °C	Min.	400	V/µs
t_{gt}	I_{TM} = 40 A, V_D = 402 V, I_G = 20 mA, (dI_G/dt) max = 0.2 A/µs		Typ.	1.9	µs
t_q	I_{TM} = 40 A, V_D = 402 V, (d_I/dt)off = 30 A/µs, V_R = 25 V, dV_D/dt = 40 V/µs	T_j = 150 °C	Typ.	70	µs

Table 4: Static characteristics

Symbol	Test conditions			Value	Unit
V_{TM}	I_{TM} = 40 A, t_p = 380 µs	T_j = 25 °C	Max.	1.6	V
V_{TO}	Threshold voltage	T_j = 150 °C	Max.	0.82	
R_D	Dynamic resistance	T_j = 150 °C	Max.	17.5	mΩ
I_{DRM}, I_{RRM}	$V_D = V_{DRM}$, $V_R = V_{RRM}$	T_j = 25 °C	Max.	5	µA
		T_j = 125 °C		2	mA
		T_j = 150 °C		3.9	

Table 5: Thermal parameters

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case (DC)		Max.	1.0	°C/W
$R_{th(j-a)}$	Junction to ambient (DC)	S(1) = 2.5 cm2	Typ.	45	

Notes:

(1)S = Copper surface under tab

1.1 Characteristics (curves)

Figure 1: Maximum power dissipation versus average on-state current

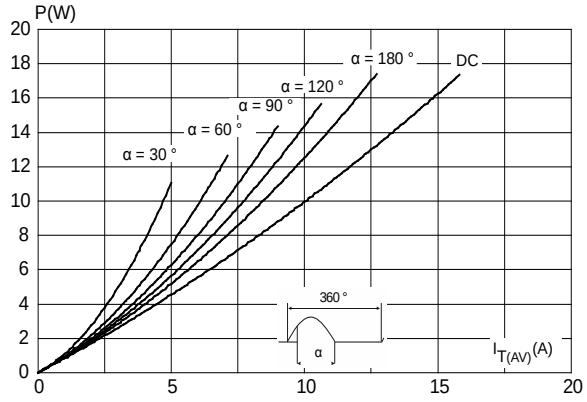


Figure 2: Average and DC on-state current versus case temperature

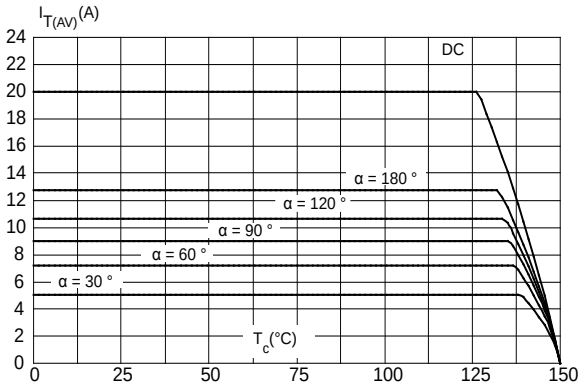


Figure 3: Average and D.C. on state current versus ambient temperature

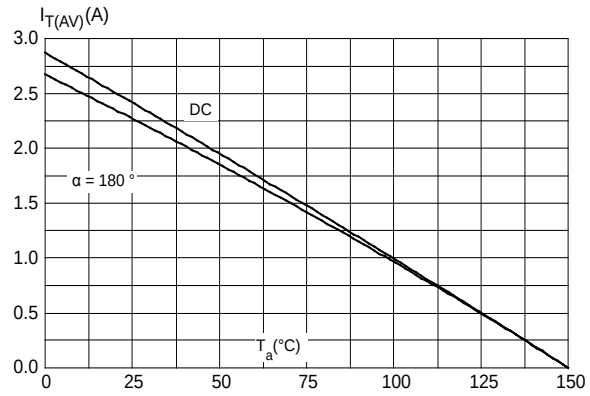


Figure 4: Relative variation of thermal impedance versus pulse duration

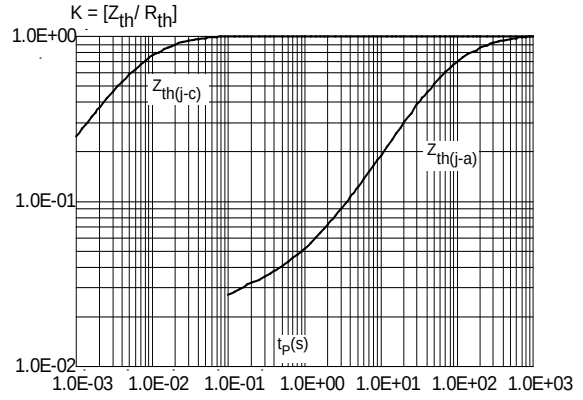


Figure 5: Relative variation of gate triggering current and gate voltage versus junction temperature (typical values)

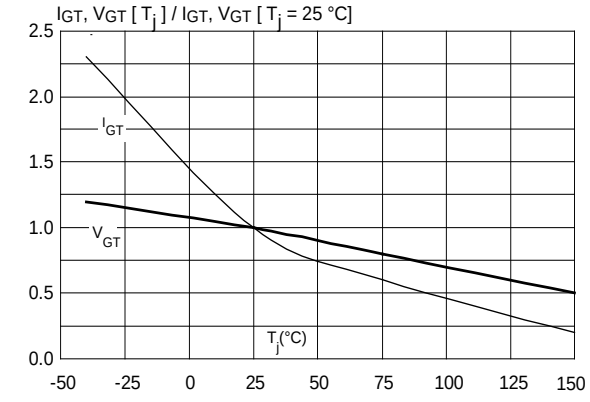


Figure 6: Relative variation of holding and latching current versus junction temperature (typical values)

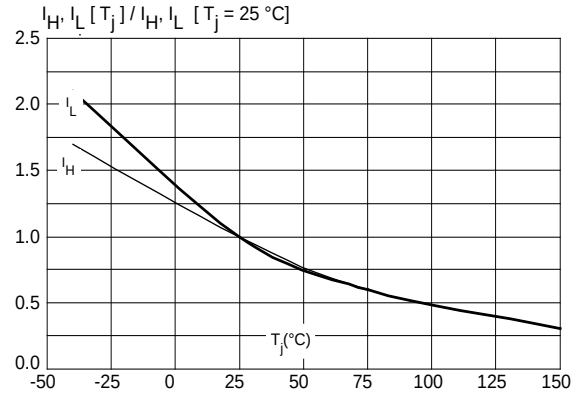


Figure 7: Relative variation of static dV/dt immunity versus junction temperature (typical values)

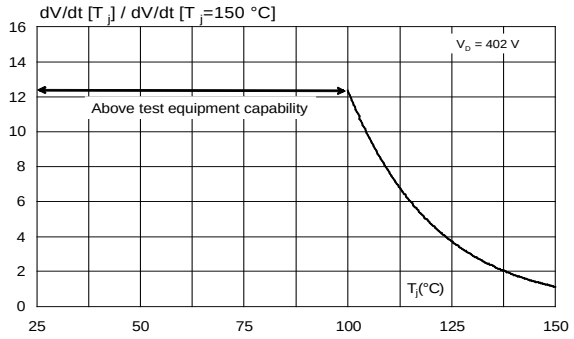


Figure 8: Surge peak on-state current versus number of cycles

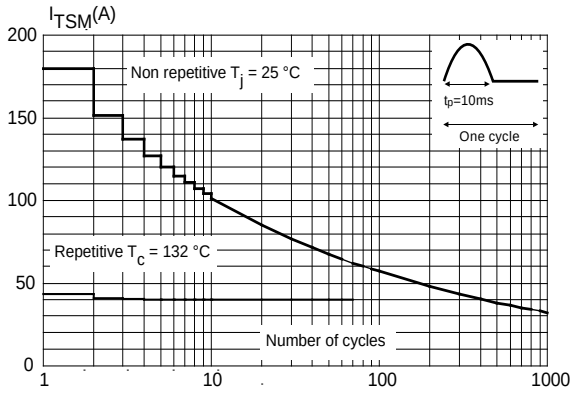


Figure 9: Non repetitive surge peak on-state current for a sinusoidal pulse with width t_p < 10 ms

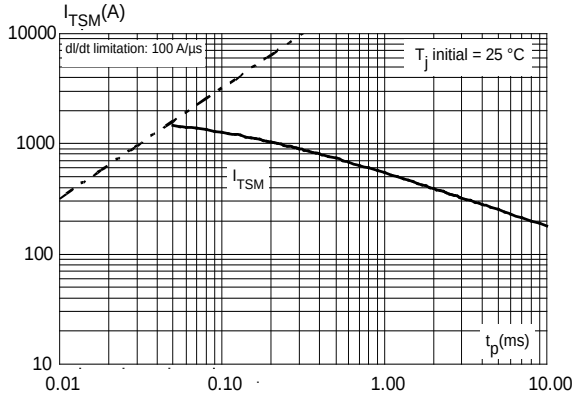


Figure 10: On-state characteristics (maximum values)

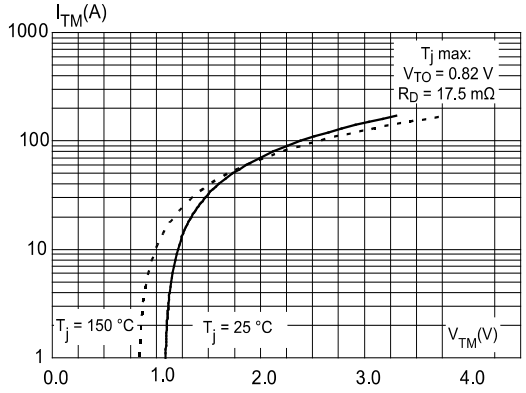


Figure 11: Relative variation of leakage current versus junction temperature

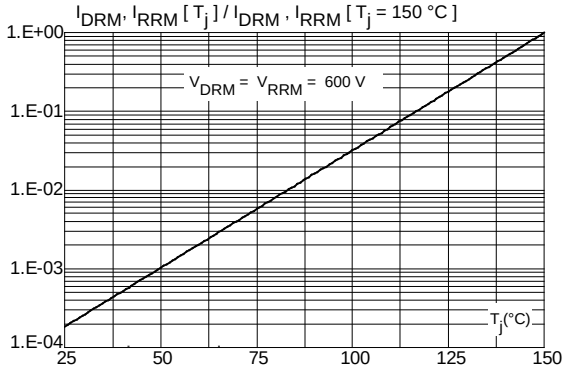
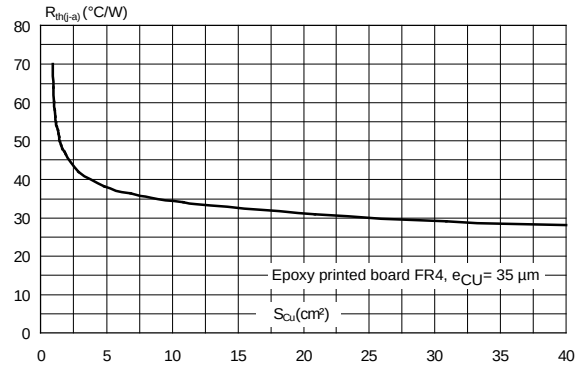


Figure 12: Thermal resistance junction to ambient versus copper surface under tab (typical values)



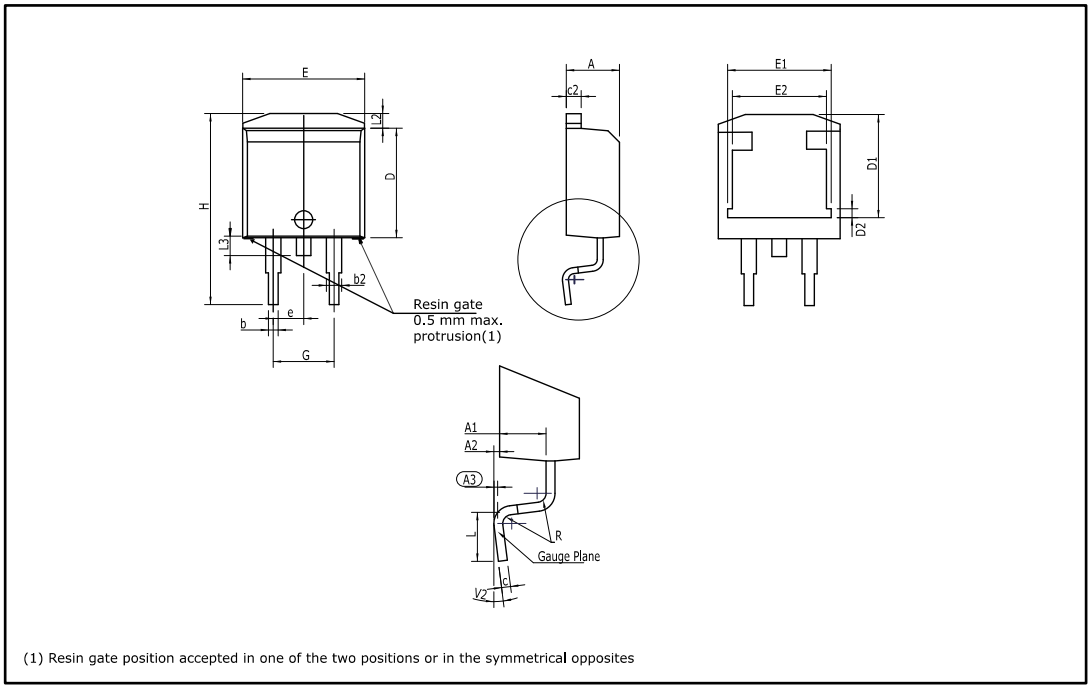
2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Lead-free, halogen-free package

2.1 D²PAK package information

Figure 13: D²PAK package outline



(1) Resin gate position accepted in one of the two positions or in the symmetrical opposites

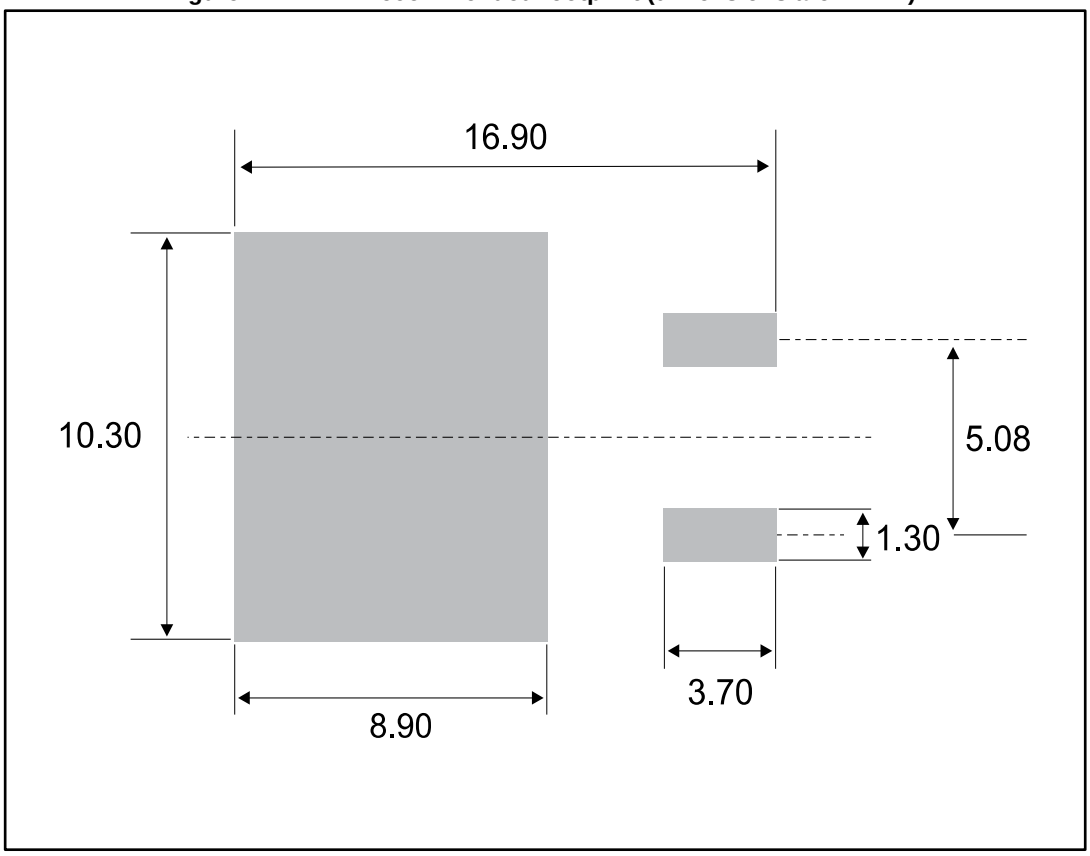
Table 6: D²PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.1693		0.1811
A1	2.49		2.69	0.0980		0.1059
A2	0.03		0.23	0.0012		0.0091
A3		0.25			0.0098	
b	0.70		0.93	0.0276		0.0366
b2	1.25		1.7	0.0492		0.0669
c	0.45		0.60	0.0177		0.0236
c2	1.21		1.36	0.0476		0.0535
D	8.95		9.35	0.3524		0.3681
D1	7.50		8.00	0.2953		0.3150
D2	1.30		1.70	0.0512		0.0669
e	2.54			0.1		
E	10.00		10.28	0.3937		0.4047
E1	8.30		8.70	0.3268		0.3425
E2	6.85		7.25	0.2697		0.2854
G	4.88		5.28	0.1921		0.2079
H	15		15.85	0.5906		0.6240
L	1.78		2.28	0.0701		0.0898
L2	1.27		1.40	0.0500		0.0551
L3	1.40		1.75	0.0551		0.0689
R		0.40			0.0157	
V2	0°		8°	0°		8°

Notes:

[1]Dimensions in inches are given for reference only

Figure 14: D²PAK recommended footprint (dimensions are in mm)



3 Ordering information

Figure 15: Ordering information scheme

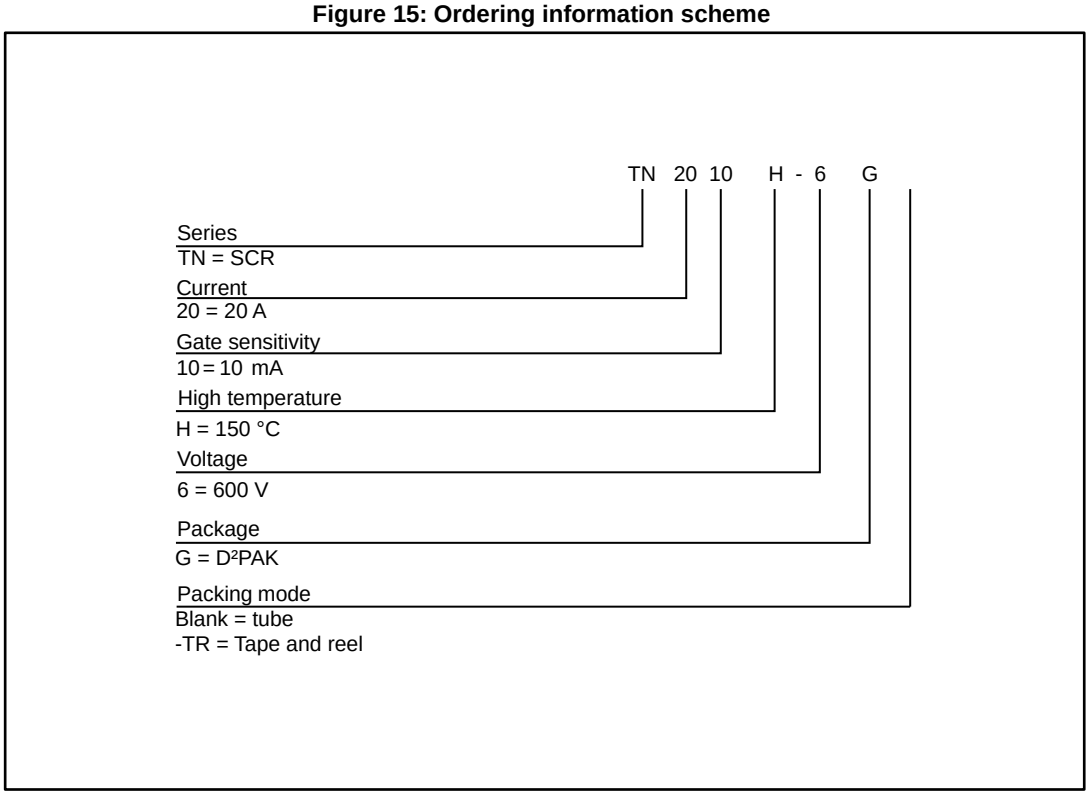


Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN2010H-6G	TN2010H6	D²PAK	2.3 g	50	Tube
TN2010H-6G-TR				1000	Tape and reel

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
24-Aug-2017	1	Initial release.

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.